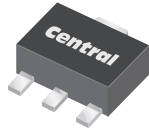


CXT591E

SURFACE MOUNT SILICON
PNP TRANSISTOR



SOT-89 CASE

Central
Semiconductor Corp.

www.centrasemi.com

DESCRIPTION:

The CENTRAL SEMICONDUCTOR CXT591E is a silicon PNP transistor manufactured by the epitaxial planar process, epoxy molded in a surface mount package, designed for high current, general purpose amplifier applications.

MARKING: FULL PART NUMBER

MAXIMUM RATINGS: ($T_A=25^\circ\text{C}$)

Collector-Base Voltage
Collector-Emitter Voltage
Emitter-Base Voltage
Continuous Collector Current
Continuous Base Current
Peak Collector Current
Power Dissipation
Operating and Storage Junction Temperature
Thermal Resistance

SYMBOL

V_{CBO} 80
 V_{CEO} 60
 V_{EBO} 5.0
 I_C 1.0
 I_B 200
 I_{CM} 2.0
 P_D 1.2
 T_J, T_{stg} -65 to +150
 Θ_{JA} 104

UNITS

V
V
V
A
mA
A
W
 $^\circ\text{C}$
 $^\circ\text{C/W}$

ELECTRICAL CHARACTERISTICS: ($T_A=25^\circ\text{C}$ unless otherwise noted)

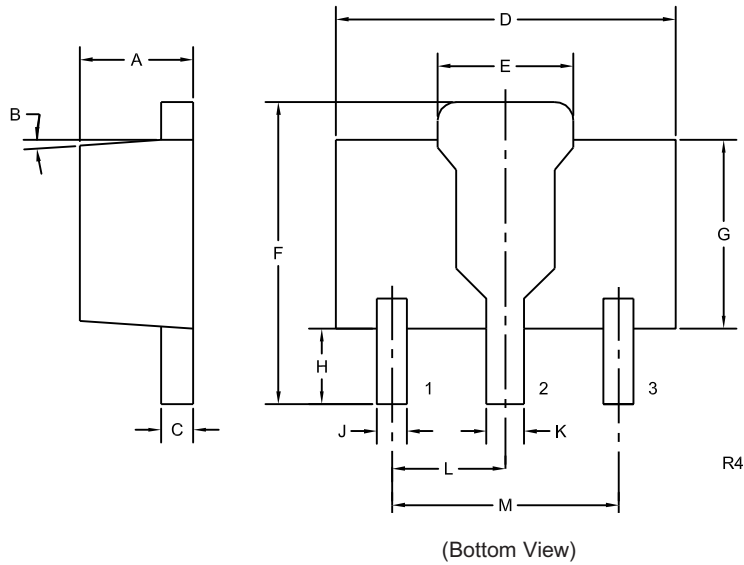
SYMBOL	TEST CONDITIONS	MIN	MAX	UNITS
I_{CBO}	$V_{CB}=60\text{V}$		100	nA
I_{EBO}	$V_{EB}=4.0\text{V}$		100	nA
BV_{CBO}	$I_C=100\mu\text{A}$	80		V
BV_{CEO}	$I_C=10\text{mA}$	60		V
BV_{EBO}	$I_E=100\mu\text{A}$	5.0		V
$V_{CE(SAT)}$	$I_C=500\text{mA}, I_B=50\text{mA}$		0.20	V
$V_{CE(SAT)}$	$I_C=1.0\text{A}, I_B=100\text{mA}$		0.40	V
$V_{BE(SAT)}$	$I_C=1.0\text{A}, I_B=100\text{mA}$		1.1	V
$V_{BE(ON)}$	$V_{CE}=5.0\text{V}, I_C=1.0\text{A}$		1.0	V
h_{FE}	$V_{CE}=5.0\text{V}, I_C=1.0\text{mA}$	200		
h_{FE}	$V_{CE}=5.0\text{V}, I_C=500\text{mA}$	200	600	
h_{FE}	$V_{CE}=5.0\text{V}, I_C=1.0\text{A}$	50		
h_{FE}	$V_{CE}=5.0\text{V}, I_C=2.0\text{A}$	15		
f_T	$V_{CE}=10\text{V}, I_C=50\text{mA}, f=100\text{MHz}$	150		MHz
C_{ob}	$V_{CB}=10\text{V}, I_E=0, f=1.0\text{MHz}$		10	pF

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CXT591E
SURFACE MOUNT SILICON
PNP TRANSISTOR



SOT-89 CASE - MECHANICAL OUTLINE



LEAD CODE:

- 1) Emitter
- 2) Collector
- 3) Base

MARKING:

FULL PART NUMBER

SYMBOL	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.055	0.067	1.40	1.70
B	4°		4°	
C	0.014	0.018	0.35	0.46
D	0.173	0.185	4.40	4.70
E	0.064	0.074	1.62	1.87
F	0.146	0.177	3.70	4.50
G	0.090	0.106	2.29	2.70
H	0.028	0.051	0.70	1.30
J	0.014	0.019	0.36	0.48
K	0.017	0.023	0.44	0.58
L	0.059		1.50	
M	0.118		3.00	

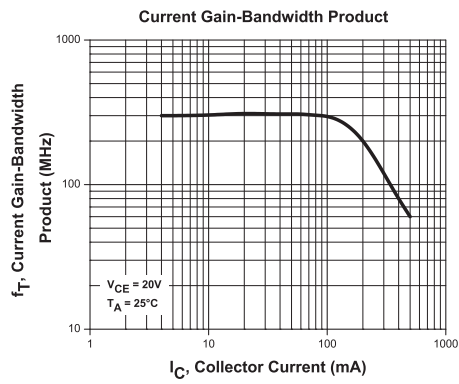
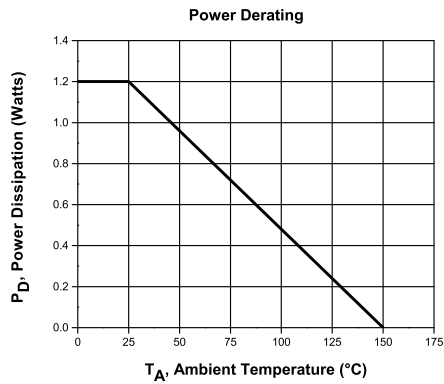
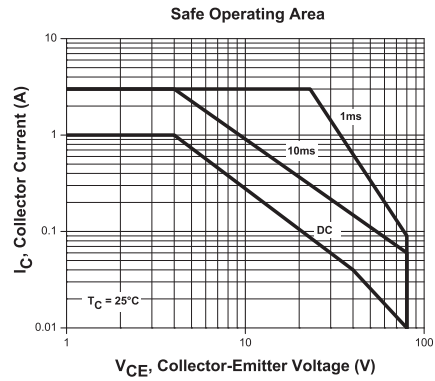
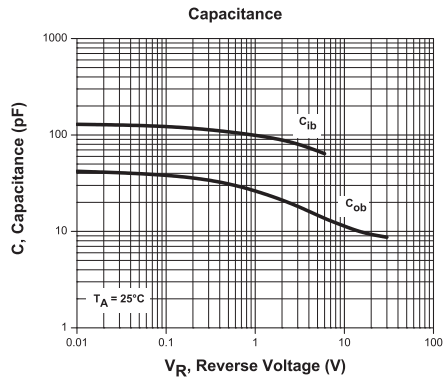
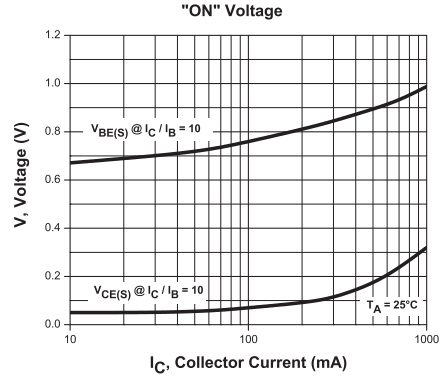
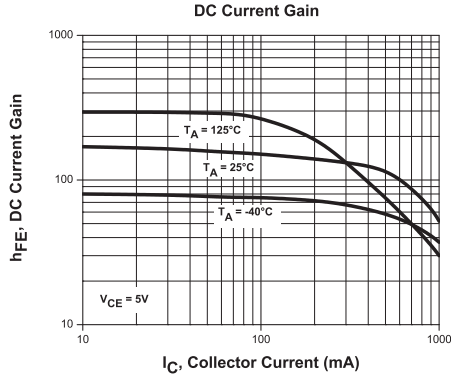
SOT-89 (REV: R4)

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CXT591E
SURFACE MOUNT SILICON
PNP TRANSISTOR



TYPICAL ELECTRICAL CHARACTERISTICS



R2 (11-June 2013)